

Ferromagnetic Materials for Josephson π Junctions

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The past two decades have seen an explosion of work on Josephson junctions containing ferromagnetic materials. Such junctions are under consideration for applications in digital superconducting logic and memory. In the presence of the exchange field, spin-singlet Cooper pairs from conventional superconductors undergo rapid oscillations in phase as they propagate through a ferromagnetic material. As a result, the ground-state phase difference across a ferromagnetic Josephson junction oscillates between 0 and π as a function of the thickness of the ferromagnetic material. π -junctions have been proposed as circuit elements in superconducting digital logic and in certain qubit designs for quantum computing. If a junction contains two or more ferromagnetic layers whose relative magnetization directions can be controlled by a small applied magnetic field, then the junction can serve as the foundation for a memory cell. Success in all of those applications requires careful choices of ferromagnetic materials. Often, materials that optimize magnetic properties do not optimize supercurrent propagation, and vice versa. In this review we discuss the significant progress that has been made in identifying and testing a wide range of ferromagnetic materials in Josephson junctions over the past two decades. The review concentrates on ferromagnetic metals, partly because eventual industrial applications of ferromagnetic Josephson junctions will most likely start with metallic ferromagnets (either in all metal junctions or junctions containing also an insulating layer). We will briefly mention work on non-metallic barriers, including ferromagnetic insulators, and some of the exciting work on spin-triplet supercurrent in junctions containing noncollinear magnetic inhomogeneity.

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I. INTRODUCTION

It has been over 20 years since Ryazanov and co-workers first demonstrated a magnetic Josephson junction whose ground-state phase difference could be either zero or π depending on the sample temperature.^{1,2} That breakthrough was followed soon after by Kontos *et al.*, who demonstrated the $0 - \pi$ transition as a function of the thickness of the ferromagnetic material in a series of magnetic junctions.³ The evidence for the $0 - \pi$ transition in those pioneering works was indirect in the sense that only the amplitude of the critical current was measured; direct measurements of the junction phase were carried out soon thereafter.⁴⁻⁷ The physical mechanism underlying these phenomena had been understood already 20 years earlier;⁸⁻¹⁰ nevertheless, the laboratory demonstrations of these phenomena sparked widespread interest in magnetic Josephson junctions and in π -junctions in general.¹¹⁻¹³ There have been many proposals to use π -junctions as circuit elements in superconducting digital logic^{14,15} and in certain qubit designs for quantum computing,^{16,17} and several of these ideas are being tested in the laboratory (see Section III of this review).

At about the same time as the first π -junction demonstrations, Bergeret, Volkov and Efetov predicted theoretically that magnetic Josephson junctions made from conventional spin-singlet superconductors could carry long-range spin-triplet supercurrent under specific conditions that include the presence of non-collinear magnetic inhomogeneities inside the junctions.¹⁸⁻²¹ Unlike the demonstration of magnetic π junctions, the Bergeret prediction came as a total surprise to the superconductivity community. The idea that supercurrents could be spin-polarized led to much excitement and the coining of the name “superconducting spintronics” for this new area of condensed matter physics.²²⁻²⁶

Put together, the two breakthroughs mentioned above catalyzed a huge surge in interest in superconducting/ferromagnetic (S/F) hybrid systems. This review covers only a small subset of the work that has been done since 2001, focusing mainly on S/F/S π -junctions and their variants, including S/I/F/S, S/I/s/F/S and S/FI/S junctions (where I = insulator and FI = ferromagnetic insulator). Our emphasis is on the wide range of magnetic materials that have been used in such devices. The centerpiece of the review are the Tables in Section IV, which we hope provide a complete list of magnetic materials that have been used inside Josephson junctions, usually with the aim of making π -junctions. To our knowledge, the last time such a compilation has been made was in 2006 by Kupriyanov, Golubov, and Siegel.²⁷

That review covered both experimental and theoretical developments; ours focuses almost entirely on experimental results.

There has been a lot of work on other experimental signatures of S/F physics besides π -state Josephson junctions, such as the critical temperature and critical field of S/F bilayers and multilayers. We do not discuss those results here, even though some of that work^{28–36} predated the experimental demonstrations of π Josephson junctions discussed above.

The structure of this review is as follows: Section II discusses general considerations, including the physical parameters that describe Josephson junctions, ballistic vs diffusive transport regimes, the different types of junctions, and how the junction response to a magnetic field is modified when the junction contain ferromagnetic materials. Section III discusses applications of π -junctions in quantum and classical circuits. Section IV discusses metallic S/F/S π -junctions and contains the Tables of magnetic materials mentioned above. It includes a short subsection about “spin-valve” junctions whose critical current or phase state are controllable by changing the magnetic configuration inside the junction. Section V mentions briefly the many different types of π -junctions that have been created in the past few years in exotic materials other than metals. Section VI discusses spin-triplet Josephson junctions, including a very brief mention of so-called “ ϕ and ϕ_0 -junctions.” Finally, Section VII contains a discussion of some open challenges and directions for the future.

II. GENERAL CONSIDERATIONS

A. S/F physics, length scales, and theoretical predictions for $I_c R_N$

The physics of S/F systems has been reviewed many times;^{11–13,21,23} we encourage readers new to the topic to read the excellent pedagogical article by Demler *et al.*³⁷ Superconducting and ferromagnetic materials in contact or in close proximity to each other interact in two distinct ways. Effects due to the magnetic field produced by F are generally referred to as “orbital effects”; they are nearly always present in experiments and should not be forgotten, but they are not the main focus of this review. Here we focus on proximity effects, whereby electron pair correlations are induced in a material in contact with a superconductor.

We start by defining several important length scales. The superconducting coherence length is defined as $\xi_S^{bal} = \hbar v_F / \Delta$ or $\xi_S^{dif} = (\hbar D_S / \Delta)^{1/2}$ in the ballistic and diffusive limits,

respectively, where Δ is the superconducting gap, and v_F and D_S are the Fermi velocity and diffusion constant in S. The diffusion constant, D , is related to the electron mean free path, l , via $D = \frac{1}{3}v_F l$. In an S/N bilayer (N = normal metal), pair correlations penetrate N over a distance called the “normal-metal coherence length”, which has the following forms in the ballistic or diffusive limits: $\xi_N^{bal} = \hbar v_F / (2\pi k_B T)$ or $\xi_N^{dif} = (\hbar D_N / (2\pi k_B T))^{1/2}$, where v_F and D_N are now in the normal metal, and T is the temperature. That length can be quite long – up to several hundred nm in noble metals at dilution refrigerator temperatures. In contrast, in ferromagnetic materials the pair correlations oscillate in sign due to the exchange splitting between the majority and minority spin bands in F. (Those oscillations are sometimes referred to as “FFLO oscillations” after Fulde-Ferrell³⁸ and Larkin-Ovchinnikov,³⁹ but we emphasize that the original FFLO prediction was for a bulk ferromagnetic superconductor in the ballistic limit, rather than a proximity system.) The period of the oscillations is $2\pi\xi_F$, where ξ_F is sometimes called the “exchange length” or the “ferromagnetic coherence length”. In the ballistic or diffusive limits with $E_{ex} \gg k_B T$, the results are $\xi_F^{bal} = \hbar v_F / (2E_{ex})$ or $\xi_F^{dif} = (\hbar D_F / E_{ex})^{1/2}$, respectively, where $2E_{ex}$ is the exchange splitting between the majority and minority spin bands. In addition to the oscillation, the pair correlations decay algebraically in the ballistic limit or exponentially in the diffusive limit. Due to the large exchange energies in strong F materials, $E_{ex} \approx 1\text{eV}$, ξ_F is less than 1 nm in those materials. That is one reason why experimental progress in S/F systems lagged behind the theoretical developments for so long. One of the keys to the experimental breakthroughs of 2001 was the use of dilute ferromagnetic alloys: CuNi alloy in the case of the Ryazanov group² and PdNi alloy in the case of the Aprili group.^{3,40} Diluting the Ni decreased E_{ex} substantially thereby increasing ξ_F to values of several nm. In that limit one must include the contribution of the temperature to the exchange length ξ_F ; in fact, Ryazanov’s first demonstration of a π -junction was carried out by varying the temperature of a Josephson junction with fixed ferromagnetic layer thickness.²

When discussing the critical current, I_c , of Josephson junctions, we will quote results for the $I_c R_N$ product, where R_N is the normal-state resistance of the junction, usually determined from the slope of the I - V relation for applied currents $I \gg I_c$. $I_c R_N$ is a useful quantity because it is independent of junction area and because it can be compared with the standard Ambegaokar-Baratoff result for short S/I/S junctions: $I_c R_N = \pi\Delta / (2e)$.⁴¹ Calculations of I_c for ferromagnetic Josephson junctions have been carried out in several

different regimes. In addition to the length scales defined above, one must also consider the electron mean free path, l_F , and the thickness d_F of the F layer. The first calculation of $I_c R_N$ was performed for the purely ballistic or “clean” limit, defined by $d_F \ll \xi_S \ll l_F, l_S$ – i.e. neglecting impurity scattering in both F and S.⁹ The decay and oscillations of $I_c R_N$ are given by the numerical maximum with respect to φ of the ballistic limit supercurrent $I_S(\varphi)$,⁹

$$I_S(\varphi)R_N = \frac{\pi\Delta\alpha^2}{2e} \int_{\alpha}^{\infty} \frac{dy}{y^3} \left[\sin\left(\frac{\varphi-y}{2}\right) \tanh\left(\frac{\Delta \cos\frac{\varphi-y}{2}}{2k_B T}\right) + \sin\left(\frac{\varphi+y}{2}\right) \tanh\left(\frac{\Delta \cos\frac{\varphi+y}{2}}{2k_B T}\right) \right], \quad (1)$$

where φ is the phase difference across the junction, and $\alpha \equiv d_F/\xi_F^{bal}$. In the limit of large α and for T near T_c , Eqn. 1 can be simplified to,⁹

$$I_c R_N = \frac{\pi\Delta^2}{4eT} \left| \frac{\sin(d_F/\xi_F^{bal})}{(d_F/\xi_F^{bal})} \right|. \quad (2)$$

The simplified form of the ballistic limit shows $0 - \pi$ oscillations at $d_F/\xi_F^{bal} = n\pi$, but misses the first transition, which occurs at $d_F/\xi_F^{bal} \approx 0.33\pi$.

The opposite limit is the diffusive or “dirty” limit, defined by $l_F, l_S \ll d_F, \xi_S, \xi_F$ – i.e. the limit where impurity scattering is very strong in both F and S. In that limit the Usadel equation is valid, and the original calculation produces the result:^{10,13}

$$I_c R_N = \frac{\pi\Delta^2}{4eT_c} 2x \left| \frac{\cos(x) \sinh(x) + \sin(x) \cosh(x)}{\cosh(2x) - \cos(2x)} \right|, \quad (3)$$

where $x = d_F/\xi_F^{dif}$. In the limit $d_F \gg \xi_F^{dif}$ and T near T_c , that result simplifies to:^{10,13}

$$I_c R_N = \frac{\sqrt{2}\Delta^2}{4eT_c} \left(\frac{d_F}{\xi_F^{dif}} \right) \exp\left(\frac{-d_F}{\xi_F^{dif}}\right) \left| \sin\left(\frac{d_F}{\xi_F^{dif}} + \frac{\pi}{4}\right) \right|, \quad (4)$$

which predicts $0 - \pi$ oscillations at $d_F/\xi_F^{dif} = (n + 3/4)\pi$.

There are several ways in which real Josephson junctions deviate from the strict assumptions used to calculate the expressions above. We know of only one paper that incorporates realistic models of the Fermi surfaces of the S and F materials into a calculation of I_c .⁴² In addition, strong F materials have different mean free paths for majority and minority electrons, which are not captured in the usual theoretical formulations. In the presence of

spin-flip or spin-orbit scattering in F, the length scales governing the decay and oscillations are no longer equal,^{43,44} hence one defines independent length scales ξ_{F1} and ξ_{F2} for the two phenomena. In addition, it has been shown that the position of the first $0 - \pi$ transition varies depending on the boundary conditions at the S/F interface, including the presence of an insulating barrier or a normal-metal spacer layer.^{44–46}

It is common to address some of the effects discussed above by utilizing a phenomenological expression for the diffusive regime:

$$I_c R_N = I_c R_N(0) \exp\left(\frac{-d_F}{\xi_{F1}}\right) \left| \sin\left(\frac{d_F}{\xi_{F2}} + \phi\right) \right|, \quad (5)$$

where ϕ is not necessarily equal to $\pi/4$ and $I_c R_N(0)$ is a fictitious zero thickness fit parameter. Spin-dependent scattering generally causes ξ_{F1} to decrease and ξ_{F2} to increase relative to ξ_F^{dif} , resulting in the relation $\xi_{F1} < \xi_{F2}$, which is observed in junctions containing weakly-ferromagnetic CuNi alloys, as seen in Table III.

Several authors have pointed out that the strong elemental F materials, Ni, Fe, and Co, do not satisfy the conditions of validity of the Usadel equation. In such materials the exchange energy is very large, hence the length ξ_F^{bal} is very short. Bergeret *et al.*⁴⁷ were the first to discuss the intermediate limit, defined by $\xi_F^{bal} \ll l_F \ll \xi_S^{bal}$. This limit clearly requires that $E_{ex} \gg \Delta$, which is true for the strong F materials. The expression for $I_c R_N$ in the intermediate limit involves a sum over Matsubara frequencies, which we do not reproduce here. (See Eqns. (19) and (20) in Ref. 47.) The dependence of $I_c R_N$ on d_F has a similar form to Eqn. (5), except now one finds that the oscillation period is governed by the ballistic expression for the exchange length, $\xi_{F2} = \xi_F^{bal}$, while the decay is governed by the mean free path, $\xi_{F1} \approx l_F$. Thus, in the intermediate limit one expects to observe $\xi_{F1} > \xi_{F2}$, which is indeed the case for many of the materials listed in Table I.

When it comes to fitting experimental data, one requires data over a wide range of thicknesses to obtain accurate estimates of all the parameters in Eqn. (5). If only a single $0 - \pi$ transition is observed in the measured thickness range, then the parameters ξ_{F2} and ϕ have large uncertainties and are highly correlated. To remove that correlation, we prefer to use the following fitting form:

$$I_c R_N = I_c R_N(0) \exp\left(\frac{-d_F}{\xi_{F1}}\right) \left| \sin\left(\frac{d_F - d_{0-\pi}}{\xi_{F2}}\right) \right|, \quad (6)$$

where $d_{0-\pi}$ is the thickness of the first $0 - \pi$ transition, which is often determined quite

accurately in the experiments. Expression (6) is the one we used when analyzing data from other groups, to extract the parameters shown in the Tables in Section IV.

B. Josephson junction geometry: planar vs “sandwich-style”

Microfabricated Josephson junctions generally take one of two geometries. In planar or lateral junctions, the supercurrent flows in the plane of the substrate, while in “sandwich-style” junctions, the current flows perpendicular to the plane. Most S/I/S junctions are of the sandwich type due to the necessity of keeping the insulating barrier extremely thin. In contrast, most S/N/S junctions studied nowadays are planar so that the supercurrent flows over a long distance in the N metal. Exceptions include junctions containing very high-resistivity metals such as silicides,⁴⁸ or junctions studied long ago on very thick alloy films.⁴⁹ Most S/F/S Josephson junctions have the sandwich structure due to the very short length scale over which the critical current oscillates and decays in ferromagnetic materials. The notable exceptions are junctions based on half-metallic CrO₂⁵⁰ or on single-crystal ferromagnetic nanowires,⁵¹ where the supercurrent may propagate over very long distances.

All of the Josephson junctions analyzed in the Tables in Section IV have the sandwich geometry.

C. S/I/F/S vs S/F/S π -junctions

Josephson junctions are characterized by several parameters. In addition to Δ and $I_c R_N$, these include the Josephson energy, $E_J = (\hbar/2e)I_c$ and the Stewart-McCumber parameter, $\beta_c = (2e/\hbar)I_c R_N^2 C$, where C is the junction capacitance. The value of β_c determines whether the junction dynamics are underdamped ($\beta_c > 1$) or overdamped ($\beta_c < 1$). Without an explicit insulating tunnel barrier, all S/F/S Josephson junctions are overdamped. They can be made underdamped by inserting an insulating barrier to make an S/I/F/S junction,^{3,52} or by using a ferromagnetic insulator (FI) as the barrier material: S/FI/S.^{53–55} The difference between overdamped and underdamped junction dynamics is crucial for all π -junction applications – both quantum and classical.

A related issue relevant for applications is whether the π -junction is being used as an active or passive device. In the former situation, the phase drop across the junction is an

important dynamical variable, whereas in the latter situation the π -junction acts as a passive phase shifter with the junction phase hardly deviating from π during circuit operation. For passive applications, the π -junction is invariably paired up with conventional S/I/S junctions whose critical currents are much smaller than that of the π -junction. That configuration is common in applications that require underdamped junction dynamics or large $I_c R_N$ product – both of which are difficult to achieve with S/F/S junctions containing a metallic barrier.

D. Dependence of critical current on applied magnetic field

A common way to assess the quality of a Josephson junction is to measure the critical current vs magnetic field applied in a direction perpendicular to the current flow, $I_c(H)$. The local supercurrent in a junction depends on the local vector potential; in the case of a uniform field, the vector potential varies linearly along the direction perpendicular to both the current and applied field.⁵⁶ For the case of a small rectangular junction of width w , with applied magnetic field, H , parallel to one of the symmetry axes, the resulting interference pattern follows the “sync” function familiar from the single-slit diffraction pattern in optics:

$$I_c(\Phi) = I_{c0} \left| \frac{\sin(\pi\Phi/\Phi_0)}{(\pi\Phi/\Phi_0)} \right| \quad (7)$$

where $\Phi_0 = h/2e = 2.07 \times 10^{-15} \text{ Tm}^2$ is the flux quantum for electron pairs, and $\Phi = \mu_0 H w (2\lambda_{\text{eff}} + d_{\text{barrier}})$ is the magnetic flux through the junction, where λ_{eff} is the effective London penetration depth of the S electrodes and d_{barrier} is the total thickness of the barrier. A small junction has w smaller than the Josephson penetration depth and thus uniform current distribution.⁵⁶ Because of the similarity with optics, a plot of such $I_c(H)$ data is colloquially referred to as the “Fraunhofer pattern.” The period of the Fraunhofer pattern in the applied field H is inversely proportional to the width w of the junction in the direction transverse to the applied field. For the case of circular junctions or elliptical junctions with the field applied along a symmetry axis, the interference pattern follows an Airy function,⁵⁶ but we still refer to the data as the Fraunhofer pattern out of habit.

The introduction of magnetic materials inside the junction leads to complications due to the field produced by the magnetic material; the Fraunhofer pattern is modified and may be severely distorted. In principle, if one knew the exact configuration of the magnetization \mathbf{M} as a function of H , one could calculate the vector potential everywhere and deduce the

$I_c(H)$ pattern.^{57,58} The converse is not true, however, except in the simplest cases discussed below. Consider first the worst situation, which is an S/F/S Josephson junction of relatively large lateral size (more than a few μm) containing a thick layer of a strong F material such as Ni, Fe, Co, or Gd. Due to the complicated multi-domain magnetic configuration of the F material, the $I_c(H)$ pattern has a random-looking set of peaks and valleys with no discernible period and no clear central peak.^{59–61} In such a situation it is neither possible to calculate the domain structure from the $I_c(H)$ data nor to deduce the maximum critical current density J_c inside the junction.

Fortunately, there exist many situations that produce well-behaved Fraunhofer patterns from which one can extract key junction parameters – in particular the maximum value of J_c . An illustrative example is the early work of Ryazanov on a Josephson junction containing a weakly-ferromagnetic CuNi alloy.⁶² That material has a mild perpendicular magnetic anisotropy (PMA),⁶³ which is advantageous because the vector potential corresponding to an out-of-plane magnetization points in the plane and does not affect the Fraunhofer pattern. In addition, if both the magnetization and domain size are small, then the vector potential effectively undergoes a random walk throughout the sample and never gets very large in magnitude. For those reasons, Ryazanov’s CuNi virgin-state junction produced an excellent Fraunhofer pattern centered at zero field. After the junction was magnetized in a large in-plane field, the Fraunhofer pattern was shifted in field with only minor distortion, indicating that the CuNi alloy had acquired a nearly-uniform in-plane component to its magnetization. After demagnetizing the sample, the Fraunhofer pattern reverted back to its original shape centered at the origin.

Even in junctions containing strong F materials, the Fraunhofer pattern is well-behaved if the magnetization of the material is uniform and parallel to the direction of the applied field H . If it stays uniform over the full measured field range, then Eqn.(7) is still valid but with a total magnetic flux that includes the contribution from the F material:

$$\Phi = \mu_0 H w (2\lambda_{\text{eff}} + d_F) + \mu_0 M (1 - N_{\text{demag}}) w d_F \quad (8)$$

where M is the magnetization of the F material and N_{demag} is the demagnetizing factor determined by the shape of the F layer. Most workers using Eqn.(8) ignore the demagnetizing factor, which is small for thin oblong-shaped F layers. Note that Eqn.(8) neglects any magnetic flux that returns inside the junction – a quantity that is difficult to calculate

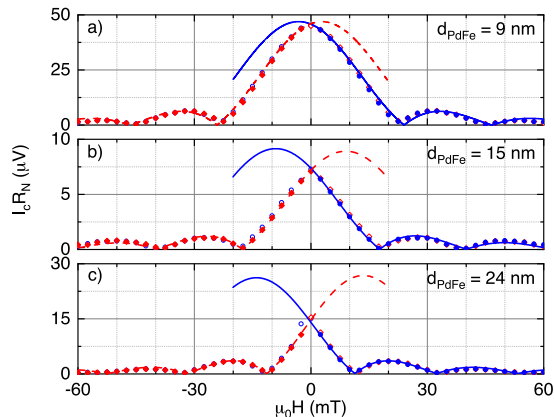


FIG. 1. $I_c R_N$ vs $\mu_0 H$ for Josephson junctions containing a PdFe alloy with 3% Fe with thicknesses labeled in the figure. Junctions have elliptical shape and lateral dimensions of $\approx 1.3 \times 0.55 \mu\text{m}^2$. The data acquired before the field at which the PdFe magnetization vector reverses direction (solid markers), and the corresponding fits (lines) show good agreement for both the positive (red, dashed) and negative (blue) field sweep directions. The hollow circles are the corresponding data points after the PdFe magnetization switches. These Fraunhofer patterns display magnetic hysteresis and are increasingly shifted with larger d_F . Adapted with permission from IEEE Trans. Appl. Supercond. 27, 1800205 (2017).⁶⁴

accurately. Setting the total flux $\Phi = 0$ shows that the central peak of the Fraunhofer pattern is shifted in field by an amount:

$$H_{shift} = \frac{-M d_F}{2\lambda_{\text{eff}} + d_F} \quad (9)$$

where we have neglected N_{demag} . Note that the denominator should also include the thicknesses of any other non-superconducting layers inside the junction – e.g. the Cu spacers used in most of the junctions studied by the authors.

We illustrate Eqn. 9 with data from junctions containing a PdFe alloy with about 3% Fe, shown in Figs. 1 and 2. We have chosen this data set because this weakly-ferromagnetic alloy has a large value of ξ_F (several nm, see Table III), hence thickness fluctuations are negligible and there is very little scatter in the data of $I_c R_N$ vs d_F . Nevertheless, the magnetization is large enough to shift the Fraunhofer patterns considerably. The PdFe thickness where $I_c R_N$ has its peak value in the π state is about 24 nm. At that thickness, the Fraunhofer pattern

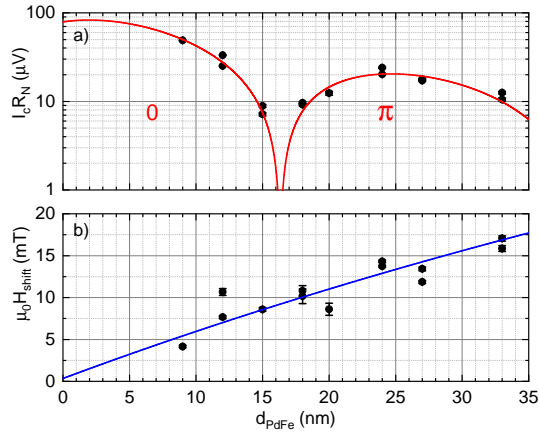


FIG. 2. Characterization of Josephson junctions containing a weakly ferromagnetic PdFe alloy. a) The maximal $I_c R_N$ product of the junctions versus PdFe thickness. The minimum indicates the PdFe thickness at which the junctions transition between the 0 and π -phase states. The solid line is a fit of the data to Eqn. 6. b) The field shift of the $I_c(B)$ data (the “Fraunhofer pattern”) vs PdFe thickness. The field shift increases with d_{PdFe} due to the increasing total magnetic moment inside the junctions and is fit to Eqn. 9. Reproduced with permission from IEEE Trans. Appl. Supercond. 27, 1800205 (2017).⁶⁴ Copyright 2017, IEEE.

is shifted by about 14 mT, and the value of I_c measured at zero field is significantly smaller than the peak value extrapolated from the fit, Figure 1 (c). Hence this material would not be ideal for π -junction applications unless the junctions were considerably narrower in their lateral dimension, with correspondingly wider Fraunhofer patterns.

III. APPLICATIONS OF π -JUNCTIONS

Several applications of Josephson junctions involve superconducting loops threaded by half a quantum of magnetic flux, which has two degenerate ground states with supercurrent circulating in opposite directions. The fundamental motivation for using a π -junction in place of the flux bias is to improve the circuit performance in some way, e.g. by reducing noise, reducing the size of the circuit (e.g. by eliminating the need for flux bias lines or a large geometrical inductance in the loop), or increasing the operating margins.

Even before Ryazanov’s 2001 experimental breakthrough with S/F/S junctions, there

already existed experimental realizations of π -junctions without magnetic materials. The most famous example involved the demonstration of the d -wave character of the high- T_c superconductors, where it was shown that a phase shift of π is created by a Pb/YBCO/Pd double-junction based on two orthogonal crystal faces of a $\text{YBa}_2\text{Cu}_3\text{O}_7$ single crystal,⁶⁵ or by three YBCO grain-boundary junctions in series.⁶⁶ π -junctions can also be realized in 4-terminal S/N/S junctions driven out of equilibrium by a control current flowing orthogonal to the supercurrent direction^{67–69} or in 3-terminal junctions with the control current injected into the junction.^{70–72} While the nonequilibrium π -junctions demonstrate fascinating physics, we would argue that they are not likely to be suitable for practical applications.

A. π -junctions in superconducting qubits

The results from d -wave superconductors^{65,66} inspired Ioffe and co-workers to propose using π -junctions in superconducting phase or flux qubits for quantum computing.^{16,17} A conventional flux qubit consists of a superconducting loop containing three Josephson junctions.^{73,74} Under an applied flux bias of exactly $\Phi_0/2$, states with clockwise and counterclockwise supercurrent flow are degenerate, and the symmetric and antisymmetric linear combinations of those states can form the two states of a qubit. Replacing the $\Phi_0/2$ flux bias with a π -junction is beneficial in several ways. In systems with many qubits the $\Phi_0/2$ flux bias can be provided either by a global magnetic field or by individual flux lines for each qubit. The former suffers from field inhomogeneity and fluctuations in loop area among the qubits while the latter suffers from crosstalk between neighboring qubits and the corresponding need to calibrate every qubit flux precisely. Both suffer from fluctuations in dc supply current. Replacing the flux bias with π -junctions alleviates those issues. In addition, removing the large static flux bias means that the qubits can be made much smaller, thereby reducing sensitivity to magnetic field fluctuations and improving prospects for large-scale integration. We note that individual flux bias lines are still needed for qubit operations, but they supply only small, pulsed currents; there is no need for a large static dc current.

The idea to use π -junctions in various types of qubits has been developed further by several authors,^{75–81} and is being pursued to this day.^{82–85} While in the early proposals, the π -junction was considered to be an active device,^{75–77} later works emphasized the advantages of using the π -junction as a passive phase-shifter,^{78,80,81,85} where the only constraint on the

critical current of the π -junction is that it be much larger than the critical currents of the conventional S/I/S junctions in the loop.

A crucial issue confronting all types of qubits is decoherence. Kato *et al.* published the first calculation of the relaxation and dephasing rates of a flux qubit containing a ferromagnetic π -junction as a passive phase shifter.⁷⁸ Those authors state explicitly that only underdamped π -junctions with very large critical current density have sufficiently long dephasing times to be suitable for qubit applications. Nevertheless, the first demonstration of a ferromagnetic π -junction in a qubit, carried out by Feofanov *et al.* in 2010,⁸⁰ used an overdamped S/F/S π -junction in series with a standard underdamped S/I/S junction to form a phase qubit. The choice of using a phase qubit rather than a flux qubit was for device simplicity. Feofanov *et al.* compared the properties of their π -junction qubit with a reference qubit without the π -junction. While there was no noticeable decrease in the decoherence time of the π -junction qubit relative to the reference qubit, both qubits had coherence times of only a few nanoseconds. Calculation of the expected decoherence time using the theoretical framework of Kato *et al.*⁷⁸ gave a result in the nanosecond range, but that theory was not intended to describe the phase qubit of Feofanov *et al.* Later, Shcherbakova *et al.*⁸¹ fabricated flux qubits with and without a π -junction and showed explicitly the shift of the magnetic-field dependence of the qubit energy splitting by exactly half of a flux quantum, but they did not measure the decoherence times of their qubits.

Very recently, Kim *et al.* fabricated and measured flux qubits with and without an S/F/S π -junction.⁸⁵ The π -junction was used as a passive phase shifter with a critical current much larger than those of the conventional S/I/S junctions in the qubit loop. The coherence time of the standard qubit was more than 1,000 times larger than that of the phase qubit studied earlier by Feofanov *et al.*⁸⁰, making this a much more stringent test of how the π -junction affects qubit performance. Kim *et al.* found that the energy relaxation time (T_1) of the flux qubit decreased from about $15\mu\text{s}$ to $1.5\mu\text{s}$ upon insertion of the π -junction, while the value of T_2 decreased from about $11\mu\text{s}$ to $1.5\mu\text{s}$. The authors attribute the decreases to dissipation in the S/F/S junction due to quasiparticle excitations. While these results are somewhat disappointing, they are not surprising given the insistence by Kato *et al.* that only underdamped π -junctions are suitable for use in quantum circuits, even when the π -junction is used as a passive phase shifter.⁷⁸ Kim *et al.* suggest using a π -junction based on a ferromagnetic insulator (FI) rather than a metallic ferromagnet, and we certainly agree.

Unfortunately, the only FI that has been studied extensively in Josephson junctions is GdN, where a number of complex behaviors have been observed. We delay our discussion of GdN Josephson junctions to Section V of this review. Another possibility would be to use an S/I/F/S junction, if the critical current density can be made large enough and the damping small enough to satisfy the requirements laid out by Kato *et al.*

Nowadays it is possible to fabricate so-called “fluxonium” qubits with coherence times as large as a millisecond.⁸⁶ Like traditional flux qubits, fluxonium qubits also have an optimal working point when flux biased at $\Phi_0/2$.⁸⁷ It would be very informative to repeat the experiment of Kim *et al.* on a fluxonium qubit, but with an underdamped S/FI/S or S/I/F/S π -junction in place of Kim’s S/F/S π -junction.

B. π -junctions in superconducting digital logic

A more promising application of π -junctions, in our opinion, is in superconducting digital electronics.^{88,89} There have been numerous proposals for using π phase shifters in superconducting digital circuits, starting with the pioneering papers by Terzioglu and Beasley in 1998¹⁴ and Ustinov and Kaplunenko¹⁵ in 2003, and continuing to the present.^{90–108} The initial motivation for introducing π -junctions into single-flux-quantum (SFQ) digital logic circuits was to eliminate the need for the large geometrical loop inductances needed to store single flux quanta, thereby reducing the circuit size substantially.¹⁵ Subsequently it was argued that incorporating π -junctions could also alleviate the need for current bias lines and increase circuit operating margins.⁹⁰ More recently, entire new families of superconducting digital logic incorporating π -junctions are being explored, as we will see below.

The distinction between active and passive roles of the π -junction is crucial in this context of classical digital circuits, just as it was in qubits. The speed at which a Josephson junction switches into the voltage state is limited by the time $\tau_{switch} = \hbar/(eI_c R_N)$. Metallic S/F/S π -junctions without an insulating barrier have very low values of $I_c R_N$, hence they are not suitable as switching elements in high-speed circuits. The easiest way around that problem is to use S/F/S junctions only as passive phase shifters embedded in circuits that contain conventional S/I/S junctions.⁸⁰ The critical current of the S/F/S phase shifter must be considerably larger than that of the S/I/S junctions, so that the S/F/S junction never switches into the voltage state and its phase drop stays close to π . An alternative approach

is to develop π -junctions with a large $I_c R_N$ product. That is not trivial; simply adding an insulating barrier increases the value of R_N by a large factor but simultaneously decreases I_c – usually by a larger factor.⁵² An ingenious solution is to insert a thin superconducting layer between the insulating barrier and the F layer, to get S/I/s/F/S.^{109–112} Depending on the thickness of the “s” layer, the S/I/s/F/S behaves either as a single Josephson junction with large $I_c R_N$ product, or as a series combination of a standard S/I/S junction and an S/F/S junction.

The first laboratory demonstration of a single-flux-quantum (SFQ) digital logic circuit containing intrinsic π phase shifts was reported by Ortlepp *et al.*⁹⁰ using high- T_c /low- T_c hybrid Josephson junctions.¹¹³ The π phase shifts were introduced into superconducting loops by using orthogonal facets of the YBCO a-b plane, as was done in the original measurement of the d -wave symmetry in YBCO.⁶⁵ Ortlepp *et al.*⁹⁰ demonstrated proper functioning of a toggle flip-flop circuit, and they used circuit simulations to compare two identically-functioning circuits with and without π phase shifters. The circuit with the phase shifters contained fewer current bias lines, took up considerably less area, and had wider operating margins – i.e. better stability against variations in circuit parameters. Shortly thereafter, Balashov *et al.*¹¹⁴ demonstrated an all-niobium toggle flip-flop with a π phase shifter based on the “trapped flux” method.¹¹⁵ The π phase shifter replaces a large geometrical inductance, hence diminishes the circuit size substantially. Using the same type of trapped-flux π -shifter, Wetzstein *et al.* compared the bit error rates of toggle flip-flops with and without a π phase shifter, and concluded that the former had improved robustness against circuit noise.⁹³

The first demonstrations of all-Nb SFQ circuits containing ferromagnetic π -junctions were reported by Feofanov *et al.*⁸⁰ and by Khabipov *et al.*⁹² in 2010. Those works represent a major milestone because all modern large-scale SFQ circuits are fabricated using only Nb-based superconductors, and because they represent the first example of a scalable process for incorporating π -junctions into SFQ circuits. In comparison to trapped-flux π -shifters, S/F/S junctions are more compact and do not require a delicate initialization procedure. Both groups used the π -junction as a passive phase shifter in a circuit containing conventional S/I/S switching junctions. Both groups identified circuit size as the main advantage of using π -junctions.

There has been a surge of interest in π -junctions in the past few years in Japan. The

Yoshikawa group at Yokohama University has shown through simulations that including π -junctions in certain SFQ circuits reduces the junction count significantly, while the new circuits have wider operating margins and lower static power dissipation than their conventional counterparts.^{95,98} They and others propose similar advantages using π -junctions in ultra-low-power adiabatic quantum flux parametron circuits.^{97,106,108} The Fujimaki group at Nagoya University recently invented a new family of superconducting logic called “half-flux-quantum” logic, where information propagates in the form of voltage pulses with area equal to $\Phi_0/2$ rather than Φ_0 as in standard SFQ circuits.^{94,96,100–104} The basic unit of half-flux quantum logic was originally a $0 - \pi$ SQUID, where the 0 -junction and π -junction in the SQUID must have similar critical currents and switching properties. The inventors soon realized, however, that it is more practical to use a $0 - 0 - \pi$ SQUID instead, where the π -junction is used as a passive phase shifter and never switches into the voltage state. Half-flux-quantum circuits offer several advantages compared to standard SFQ circuits, including smaller bias currents, smaller circuit size, and lower power dissipation.

Another new logic family, called “phase logic”, was introduced very recently by the group at Moscow State University.^{105,107} A major selling point of phase logic is the absence of inductors, which take up much of the space in standard SFQ circuits and cause crosstalk between neighboring cells, thereby being a major hindrance to scaling those circuits to smaller sizes. In the original proposal, phase logic circuits were based on bistable Josephson junctions with a dominant second harmonic in their current phase relation: $I_s(\phi) = I_c \sin(2\phi)$. The existence of such junctions has been demonstrated in special situations,^{116,117} and proposed to exist in others,^{118–121} but we emphasize that they are not available as “off the shelf” components ready for use in electronic circuits. Hence it was encouraging when Maksimovskaya *et al.*¹⁰⁷ suggested a way to construct phase logic circuits using standard π -junctions. Phase logic appears to be a promising avenue for scaling superconducting circuits to higher densities, and is being pursued also by circuit designers in the US.^{122–125}

We note that the $0 - 0 - \pi$ SQUIDs that form the basic unit of the Nagoya group’s half-flux-quantum logic are equivalent to a single junction with a negative second harmonic current-phase relation: $I_s(\phi) = -I_c \sin(2\phi)$.¹⁰⁵ The ground state of such a SQUID is doubly-degenerate, with a phase shift of $\pm\pi/2$ across the SQUID. In contrast, the basic unit of the Moscow group’s original phase logic proposal is a junction with a positive second harmonic current-phase relation, which puts its ground state phase at either 0 or π . Those two

situations have very different consequences for circuit design.

C. Controllable junctions: superconducting memory

Josephson junctions with controllable properties are suitable for applications in superconducting memory. The controllable property can be either the magnitude of I_c or the phase state of the junction, but in the former case the junction must be active, i.e. it must switch into the voltage state when the applied current surpasses I_c , which means it must have a large $I_c R_N$ product for high-speed operation, as discussed earlier.

There are several proposals for controlling the magnitude of I_c in Josephson junctions containing a single magnetic layer. The Ryazanov group developed controllable S/F/S junctions containing a weakly-ferromagnetic PdFe alloy.¹²⁶ In a collaboration with the Hypres Corporation in the US, that idea was extended to controllable S/I/s/F/S junctions with a large $I_c R_N$ product.^{109,110} Control of I_c was achieved by the orbital effect – i.e. by shifting the Fraunhofer pattern of the junction via partial magnetization of the PdFe. A disadvantage of that approach is that it does not scale well as the junction size is reduced. The junction size can be reduced in one in-plane dimension, but must remain large in the other dimension to achieve adequate Fraunhofer shift.¹²⁷ A recent proposal to control I_c via the stray field produced by the magnetic texture of a Co disk also relies on the orbital effect, but the constraints on junction size are less severe because of the large magnetization of the Co.¹²⁸

Several other schemes for controlling I_c of Josephson junctions have been proposed, and we do not try to review all of them here. We mention one based on placing Abrikosov flux vortices in close vicinity to a Josephson junction,¹²⁹ one based on rotating the magnetization in a combination S/F/S and S/F/N/S device,¹³⁰ and another based on a multiterminal S/F device.^{131,132}

The possibilities become richer when there are two independent F layers inside the junction – one with fixed magnetization and the other with a magnetization that can be reoriented by application of a small external field. Either the magnitude of I_c or the phase state of the junction can be controlled in such junctions, as predicted in a number of theoretical works.^{133–141} The first experimental verification of I_c modulation in such “spin-valve” junctions was performed by Bell *et al.* in 2004, using Co and Ni₈₀Fe₂₀ (NiFe) as the fixed and

free F layer materials, respectively.¹⁴² A similar experiment was revisited a decade later in a much more thorough study by Baek *et al.*,¹⁴³ and also by Qadar *et al.*¹⁴⁴ Those groups used NiFe-based alloys as the free layer because of their excellent magnetic switching properties, even though they are not so great for supercurrent transmission (see Table II). Baek *et al.* used Ni as the fixed layer material since Ni has the best supercurrent transport of any strong F material (see Table I in Section IV).

Controlling the phase state of the junction rather than the amplitude of I_c has two advantages. First, there is no need for a large $I_c R_N$ product, which is difficult to achieve in all-metal junctions. Second, the junction phase is intrinsically a digital rather than analog quantity; it can take only one of the two values zero or π , as long as the F-layer is far from the thickness corresponding to the $0 - \pi$ transition. The first demonstration of phase control in spin-valve junctions was carried out by one of the authors and his students,^{145,146} using Ni and NiFe for the fixed and free F-layer materials. Similar junctions formed the basis for Northrop Grumman’s “Josephson Magnetic Random Access Memory” or JMRAM, which was demonstrated on a 2×2 memory array in 2017.¹⁴⁷ A later demonstration on an 8×8 memory array revealed a difficulty with this approach, namely the inconsistent behavior of the magnetic layers in different memory cells. The Ni fixed layers are multi-domain at the μm -scale lateral dimensions of the junctions, and require a very large initialization field to magnetize completely.¹⁴³ And the switching fields of the NiFe free layers varied significantly from cell to cell. A great deal of materials research would be needed to turn this idea into a successful memory technology.

Finally, we mention proposals that involve intrinsic bistability of I_c or of the junction phase state without requiring any change in the magnetic configuration.^{148,149}

IV. METALLIC π -JUNCTIONS

The Tables in this section are intended for the reader to make quick comparisons between materials and works. We attempt to include as much of the available literature as possible, even where fit parameters could not be extracted from the data; hence there are gaps in the Tables. We present four Tables on single F layer junctions: I – pure elements, II – NiFe and NiFe-based alloys, III – weak ferromagnetic alloys, and IV – strong and other ferromagnetic alloys. Within each Table, materials are grouped together, and where there are multiple

works on the same material, the works are listed chronologically.

The methodology for putting together the Tables in this section is as follows. Fit parameters are either extracted from the original publications, or datasets are extracted from the plotted graphs, fit to Eqn. 6 and the best fit parameters are reported in the Table. We fit the expression only to the nominal thickness of the ferromagnetic layer, ignoring magnetic dead layers and any role of additional buffer layers. The reported uncertainties in the original datasets are not taken into consideration for the fitting, so we quote all fit parameters to 2 significant figures without consideration of their uncertainties. For more rigorous data analysis, the reader should refer to the published works, particularly for cases where Eqn. 6 does not provide the best fit to the experimental data. We attempt to note in the main text and figure captions as much as possible where subtleties exist in the experimental data which are not accounted for in the fitting here.

The parameters we report in the Tables include the fit parameters from Eqn. 6, corresponding to the decay and oscillation lengths ξ_{F1} and ξ_{F2} , the thickness at which the first $0-\pi$ transition occurs, $d_{0-\pi}$, and the fictitious zero thickness fit parameter, $I_c R_N(0)$, which is necessary for the reader to reproduce the fits but doesn't have a physical meaning. (Junctions without the ferromagnet will not have the extracted $d_F = 0$ critical current as there are fewer interfaces in such devices.) We also extract the critical current at the peak of the π -state, which is a useful parameter for device consideration and for comparing materials. When the range of thicknesses studied is not broad enough to cover multiple $0-\pi$ oscillations (multiple minima in $I_c R_N$), the ξ_{F2} fitting parameter is ambiguous, in which case that parameter will be missing from the Tables.

There are two common conventions for reporting the magnitude of critical Josephson current. The first is the product of the critical current and normal state resistance, $I_c R_N$, quoted here in μV . The second convention is to report the critical current density, J_c , quoted here in kAcm^{-2} . The main difference between $I_c R_N$ and J_c is that the junction area need not be known to report $I_c R_N$, which may be advantageous for a study where multiple junction sizes are fabricated (intentionally or unintentionally). Where the original publications contain all the information necessary to perform the conversion, we report both quantities at the peak of the π -state in the Tables. Otherwise, the reader can consider the approximation that for metallic S/F/S junctions the product of area and normal state resistance, $AR_N \approx 10^{-14} \Omega\text{m}^2$, which arises primarily from the boundary resistances between

the S electrodes and the F layer.¹⁵⁰ Hence, for S/F/S junctions, one can estimate J_c by dividing $I_c R_N$ by AR_N (in the Tables, $I_c R_N$ values quoted in μV can be multiplied by 10 to get J_c in kAcm^{-2} assuming $AR_N \approx 10^{-14} \text{ }\Omega\text{m}^2$). For junctions containing an insulating layer, such as the S/I/F/S geometry, the story is very different: AR_N is typically several orders of magnitude larger, and varies widely depending on the oxidation conditions used to produce the insulating barrier.

A. Pure elements

In Table I, we highlight works studying Josephson junctions with pure elements.

Pure elemental Ni was among the first ferromagnetic barrier layers studied.¹⁵¹ Ni has the lowest bulk magnetization of the transition metal ferromagnets (550 emu/cm^3). Experimentally, it is found that Ni has favorable supercurrent carrying properties - the decay length is relatively long for a strong ferromagnet and the $I_c R_N$ is high. These favourable properties have resulted in a number of reports on Ni Josephson junctions.^{143,147,151–157,160,162,163} It is worthwhile noting that while Table I is obtained by fitting to Eqn. 6 which describes diffusive and intermediate limit transport, Ni junctions have been reported in the literature in both the diffusive¹⁵⁴ and ballistic¹⁵⁵ limits. While Ni may have favourable supercurrent carrying properties, the magnetic properties of thin Ni layers are far from ideal. Ni layers are magnetically ‘hard’, requiring a large initialization field to set the magnetization direction and a large switching field. It is well known that Ni films break up into small magnetic domains, which sets a limit on single domain junction size, and can contribute stray fields into the surrounding superconducting layers.

For determining the position of the $0 - \pi$ transition for Ni from Table I, we guide the reader towards Refs. 155 and 147, which have the smallest increments in thickness around the transitions. The data of Baek *et al.* covers both the first $0 - \pi$ and $\pi - 0$ transitions, which occur at 0.90 and 3.4 nm respectively.¹⁵⁵ The first $\pi - 0$ transition thickness is confirmed by Dayton *et al.* who observe it at 3.3 nm, again taking small increments in thickness around the transition.¹⁴⁷ Most works on Ni do not study the very thin layers of Ni in the range of Baek *et al.*’s observed $0 - \pi$ transition, and we note that in some cases it may still be possible to model the data in those works assuming $d_{0-\pi} = 0.9 \text{ nm}$.

Critical current oscillations have also been reported in pure elements of Co^{153,159,160,162}

Barrier	ξ_{F1} (nm)	ξ_{F2} (nm)	$d_{0-\pi}$ (nm)	$I_c R_N(0)$ (μV)	$I_c R_N(\pi)$ (μV)	$J_c(\pi)$ (kAcm^{-2})	dead layer (nm)	Ref.	Comments
Cu/Ni/Cu	3.8	0.98	2.6	2.8	1.0	10		151	
Cu(Au)/Ni/Cu(Au)	1.7	0.45						152	○
Ni	4.5	1.2	4.0	450	110		1.3	153	
Al ₂ O ₃ /Cu/Ni	0.66	0.53	3.0		3.7	3.4×10^{-3}	2.3	154	
Cu/Ni/Cu	2.4	0.79	0.90	330	≥ 100		0.7	155	
Cu/Ni/Cu			3.3★			200		147	○, †
Ni					> 30	> 300		156	†
Ni & Cu/Ni								157	†
Cu/Co/Cu								158	†
Co	2.1	0.29	1.0	130	65		0.8	153	
Rh/Co/Rh	0.81	0.21	0.64	260	82	1600	0.0	159	
Co/Ru/Co	1.2			2.9				61	‡
Cu/Co/Ru/Co/Cu	2.3			0.90				61	‡
Fe	5.4	0.25	0.81	170	140		1.1	160	
Al/Gd/Al	1.2			20				59	‡, 1 K
Ho	4.3			2300			2.0	161	‡

TABLE I. Extracted parameters for Nb based Josephson junctions with pure elements as the ferromagnet in the barriers. The fitting methodology to Eqn 6 is given in the main text and best fit values are quoted to 2 significant figures without consideration to their uncertainty so should be treated as approximations. The full barrier layers, including normal metals and insulators, are listed. Unless otherwise commented, the measurements were performed at 4.2 K. Comments: ○ The range of thickness values did not cover the thickness where the first 0- π transition was predicted. † The range of thickness values studied was not sufficient for a meaningful fit to theory. ‡ No 0- π oscillations were observed or claimed, and the data are fitted here with only the exponential decay component of Eqn 6. ★ This thickness corresponds to the first π -0 transition.

and Fe,^{160,164} although they are less studied than Ni. Potential advantages of Co and Fe are that thin films tend to be magnetically softer than Ni, with larger magnetic domains. An unexplored potential is that thin layers of Co can have perpendicular magnetic anisotropy when deposited on Pt or Pd normal metal spacer layers.

Finally we mention that the rare-earth metals Gd⁵⁹ and Ho¹⁶¹ have been studied in Josephson junctions, including the thickness series to extract the decay length, however no critical current oscillations attributed to the $0-\pi$ transition were observed. In the case of Gd, this may be due to the thickness increments (step size) between samples in that early work being too large to observe the oscillation. Ho has been extensively studied as a spin-triplet generator due to its intrinsic magnetic inhomogeneity,¹⁶⁵ which may make it unsuitable as a π -junction. Nb/Gd multilayers have been extensively studied for the observation of critical temperature oscillations,³³ which can guide future junction experiments. It is additionally noteworthy that Nb can seed rare-earth ferromagnet growth and that the interface is considered to be sharp with minimal interdiffusion.^{166–168}

B. NiFe alloys

In Table II, we highlight works studying Josephson junctions with NiFe and NiFe-based alloys.

Ni₈₀Fe₂₀ (hereafter NiFe) is a strong ferromagnetic alloy which is optimized for magnetic switching at small magnetic fields, making it an excellent choice in spintronics research as a soft magnetic layer. In many papers, NiFe is referred to as permalloy or Py. Josephson studies of NiFe were well motivated by the spintronics community, and it has been used as the free layer of choice in superconducting spin valves.^{142,145,147} Additional functionality offered by NiFe is the ability to set the direction of in-plane magnetic anisotropy by applying a magnetic field during growth.

From studying Table II, the reader will notice two possible positions of $d_{0-\pi}$ for NiFe, either between 1.3–1.8 nm or at 2.4 nm. We guide the reader towards the work of Dayton *et al.*,¹⁴⁷ which takes the smallest increments in thickness for NiFe around the $0-\pi$ transition and concludes that $d_{0-\pi} = 1.66$ nm, falling in the middle of the 1.3–1.8 nm range reported by other works.¹⁴⁷

Although the switching properties of NiFe at room temperature are excellent, the switching degrades at low temperatures relevant to Josephson junctions. To address this limitation, NiFe-based alloys with even lower coercivity have been developed^{174,175} and tested in Josephson junctions, such as Ni₇₃Fe₂₁Mo₀₆ (supermalloy), which we include also in Table II. Unfortunately, the decay length inside NiFe-based alloys is experimentally found to be

Barrier	ξ_{F1} (nm)	ξ_{F2} (nm)	$d_{0-\pi}$ (nm)	$I_c R_N(0)$ (μV)	$I_c R_N(\pi)$ (μV)	$J_c(\pi)$ (kAcm^{-2})	dead layer (nm)	Ref.	Comments
Cu/NiFe/Cu	1.0	0.76	2.4	360	12	170	0.7	169	#
NiFe	1.6	0.33	1.3	240	78		0.5	153	
NiFe	1.2	0.61	2.4	17	1.2			144	
Cu/NiFe/Cu	1.5	0.58	1.8	69	12	160	0.0	170	
Cu/NiFe/Cu			1.66			25		147	†
Al/AlO _x /Nb/NiFe								112	†
NiFe								171	†
Cu/NiFe/Cu	0.71	0.74	1.5	250	10	100		172	
Cu/Ni _{0.73} Fe _{0.21} Mo _{0.06} /Cu	0.48	0.96	2.3	150	0.20	1.8	0.2	173	
Cu/Ni _{0.65} Fe _{0.15} Co _{0.20} /Cu	1.1	0.48	1.2	30	5	67	0.0	170	
Cu/Ni/NiFe/Ni/Cu	0.64	0.78	0.92	800	50	530		172	

TABLE II. Extracted parameters for Nb based Josephson junctions with NiFe and NiFe-based alloys as the ferromagnet in the barriers. The fitting methodology to Eqn 6 is given in the main text and best fit values are quoted to 2 significant figures without consideration to their uncertainty so should be treated as approximations. The full barrier layers, including normal metals and in one case an additional ferromagnetic layer, are listed. Unless otherwise stated in the Table, the composition was Ni_{0.80}Fe_{0.20} and the measurements were performed at 4.2 K. Comments: # The bottom Nb electrode and barrier layers were epitaxial. † The range of thickness values studied was not sufficient for a meaningful fit to theory.

even shorter than NiFe, which reduces considerably the potential critical Josephson current of a π -junction based on these materials. This is likely due to the short electron mean free path in these alloys.

Other NiFe-based alloys which have been explored for use in Josephson junctions include Ni_{0.70}Fe_{0.17}Nb_{0.13}, which was used by Baek *et al.* as the free layer in a spin-valve device.¹⁴³ In later works, the same group used a more dilute non-magnetic concentration of the alloy as a normal metal spacer layer in junctions containing ferromagnetic Ni.^{155,163} Qader *et al.* characterized Cu_{1-x}(Ni_{0.80}Fe_{0.20})_x as a possible barrier layer, however single layer Josephson junctions with this alloy have not been reported.¹⁷⁶

The work of Bell *et al.* is noteworthy because the bottom Nb electrode and barrier layers

were grown epitaxially.¹⁶⁹ This work may, therefore, not be directly comparable to the other works in Table II. As far as we are aware, this is the only work listed in any of the Tables to study an epitaxial barrier. Epitaxy plays a role in improving the mean free path of electrons through metals, which may improve the supercurrent carrying properties of junctions with epitaxial barriers. Epitaxy has not yet been systematically studied for π -junctions and may provide fertile ground for future exploration.

C. Weak ferromagnetic alloys

In Table III, we highlight works studying Josephson junctions with weak ferromagnetic alloys.

In the context of ferromagnetic Josephson junctions, weak ferromagnet refers to materials with a low Curie temperature, and therefore low exchange energy. The structural and magnetic properties of weak ferromagnetic alloys was reviewed in detail by Kupriyanov, Golubov, and Siegel.²⁷

From Table III, the reader will notice that although CuNi alloys have been widely studied, they are far from an ideal material as a π -junction. The CuNi alloys are firmly in the diffusive limit where $\xi_{F1} < \xi_{F2}$, which in comparison to other materials presented in the Tables is somewhat of a rare case. Superconducting junctions with weak ferromagnets are a system where the theoretical Usadel equations are valid, and therefore it is possible in these systems to directly test predictions of that theoretical framework. Oboznov *et al.* apply the Usadel equations to model their data, considering that their junctions showed strong spin dependent scattering, attributed to magnetic inhomogeneities in the barrier caused by the formation of Ni-rich clusters.¹⁷⁸ Further work studying Nb/CuNi bilayers using scanning tunneling spectroscopy support this idea, finding significant spatial variation in the thickness and composition of Ni in the CuNi layer.¹⁸⁴ In comparison to CuNi, the Pd-based alloys appear much more promising as potential π -junctions due to the larger critical Josephson currents observed in the π -state.

Other works on weak ferromagnetic alloys that are not included in Table III but which we wish to highlight include an experiment where CuNi junctions were fabricated where the barrier layer has a thickness step, such that junction has both 0 and π parts.¹⁸⁵ Further work on CuNi includes observation of a positive second harmonic in the current-phase relation in

Barrier	ξ_{F1} (nm)	ξ_{F2} (nm)	$d_{0-\pi}$ (nm)	$I_c R_N(0)$ (μV)	$I_c R_N(\pi)$ (μV)	$J_c(\pi)$ (kAcm^{-2})	dead layer (nm)	Ref.	Comments
Cu ₄₈ Ni ₅₂ /Cu								2	⊗
Cu ₅₂ Ni ₄₈								177	⊗
Cu ₄₇ Ni ₅₃ /Cu	1.3	3.7	11	2200	0.15	1	4.3	178	
Al ₂ O ₃ /Cu ₄₀ Ni ₆₀	0.78	1.35	5.2		400	5.0×10^{-3}	3.1	52	2.11 K
AlO _x /Cu ₄₀ Ni ₆₀	1.2		5.8			1.5×10^{-2}		179	
AlO _x /Nb/Cu ₄₀ Ni ₆₀	1.2		7.2			6.5×10^{-2}		179	
Cu ₄₇ Ni ₅₃	1.3	4.3	7.4	3200	2.0	20		180	
NbN/Cu ₄₀ Ni ₆₀ /NbN	1.8	2.0	5.6	160	2.2	8.8		181	
Cu ₄₈ Ni ₅₂ /Al	1.3	3.2	15★		> 4.2	> 60		182	○
Al/Al ₂ O ₃ /Pd ₈₈ Ni ₁₂	2.9	2.3	6.5	450	18			3	1.5 K
Pd ₈₈ Ni ₁₂	7.7	4.4	7.4*	100				60	○
NbN/Pd ₈₉ Ni ₁₁ /NbN	4.4	3.6	8.5	540	≥ 18	≥ 71		183	
Pd ₈₉ Ni ₁₁ /Al/AlO _x					22	2.2×10^{-2}		103	†
Al/AlO _x /Nb/Pd ₉₉ Fe ₀₁								109	†
Pd ₉₇ Fe ₀₃	16.2	7.2	16	100	21	190	2.8	64	
Pt _x Ni _{1-x}								157	⊗

TABLE III. Extracted parameters for Nb based Josephson junctions with weak ferromagnetic alloy barriers. In Refs. 181 and 183, the superconductor was NbN, as indicated in the Table. The fitting methodology to Eqn 6 is given in the main text and best fit values are quoted to 2 significant figures without consideration to their uncertainty so should be treated as approximations. The full barrier layers, including normal metals and insulators, are listed. Unless otherwise commented, measurements were performed at 4.2 K. Comments: ⊗ The main focus was to study the temperature and/or compositional variation of the Josephson effect instead of the thickness dependence. † The range of thickness values studied was not sufficient for a meaningful fit to theory. * This value was extrapolated from measurements on junctions outside of this thickness. ○ The range of thickness values did not cover the thickness where the first 0- π transition was predicted. ★ This thickness corresponds to the first π -0 transition.

junctions with a CuNi thickness close to the 0 - π transition.¹¹⁶

Barrier	ξ_{F1} (nm)	ξ_{F2} (nm)	$d_{0-\pi}$ (nm)	$I_c R_N(0)$ (μV)	$I_c R_N(\pi)$ (μV)	$J_c(\pi)$ (kAcm^{-2})	dead layer (nm)	Ref.	Comments
Al/Al ₂ O ₃ /Ni ₃ Al	4.6	0.45				$\geq 1.5^\diamond$	5 - 8	186	○
Al/AlO _x /Cu/Fe _{0.75} Co _{0.25}	0.22	0.79	1.9*	> 1000	< 0.10		0.6	187	○
Pt/Co _{0.68} B _{0.32} /Pt	0.28	0.20	0.30	56	7	35	0.0	188	1.8 K
Cu/Co _{0.56} Fe _{0.24} B _{0.20} /Cu	0.10		0.80			19		189	
[Nb/Cu] _{ML} /Co _{0.56} Fe _{0.24} B _{0.20} /Cu	0.13		0.80			9.6		189	
Co _{0.40} Fe _{0.40} B _{0.20}	0.93			440				190	‡, 1.6 K
Co _{0.47} Gd _{0.53}	0.16	0.21	1.2		1.9			191	
NbN/GdN/NbN	0.40			80000				192	‡, 0.3 K
NbSe ₂ /Cr ₂ Ge ₂ Te ₆ /NbSe ₂	2.5	2.4	8.4	940	11	4.0×10^{-3}		193	1.6 K

TABLE IV. Extracted parameters for Nb based Josephson junctions with strong and other ferromagnetic alloy barriers. In Ref. 192, the superconductor was NbN and in Ref. 193, NbSe₂, as indicated in the Table. The fitting methodology to Eqn 6 is given in the main text and best fit values are quoted to 2 significant figures without consideration to their uncertainty so should be treated as approximations. The full barrier layers, including normal metals and insulators, are listed. Unless otherwise commented, measurements were performed at 4.2 K. Comments: ○ The range of thickness values did not cover the thickness where the first 0- π transition was predicted. ‡ No 0- π oscillations were observed or claimed, and the data are fitted here with only the exponential decay component of Eqn 6. ◇ This lower limit value is taken at the first observed oscillation, which is unlikely the first π -state due to the thickness range studied. * This value was extrapolated from measurements on junctions outside of this thickness.

D. Strong and other ferromagnetic alloys

In Table IV, we highlight works studying Josephson junctions with strong and other ferromagnetic alloys.

It is noteworthy that while most alloy barriers we have included in the Tables show supercurrent transport in the diffusive or intermediate limits, the Ni₃Al barrier was found to be in the ballistic limit.¹⁸⁶ The long ξ_{F1} decay length and short ξ_{F2} oscillation lengths meant that multiple 0- π oscillations in this material were accessible in the thickness range 10-18 nm. The thickness range studied was unlikely to cover the first 0- π oscillation, so we do not report a $d_{0-\pi}$ parameter for this material, and the reported $J_c(\pi)$ corresponds to

the peak of the first oscillation in the measured thickness range, so a higher $J_c(\pi)$ may be possible in thinner barriers. However, a potential downside of Ni₃Al is that the magnetic dead layer in this material was very large compared to others.

The amorphous Co-based alloys, CoFeB and CoB, are popular in spintronics and magnetic memory research due to their lack of crystalline anisotropy and weaker pinning of magnetic domain walls due to the reduced density of grain boundaries.^{188,194} For application in MRAM, they have been found to have large values of TMR when placed in magnetic tunnel junctions.¹⁹⁵ In addition, thin layers can have perpendicular magnetic anisotropy when placed on spacer layers such as Pt or Pd.^{188,194} CoGd is an amorphous ferrimagnet, where the composition can be tuned to have zero net magnetization while retaining spin-polarized transport.¹⁹⁶ In Josephson junction studies, the general conclusion from Table IV is that the amorphous alloys have very short ξ_{F1} decay length, most likely related to the short electron mean free path in amorphous metals. This limitation may make them unsuitable as π -junctions. Komori *et al.* showed that J_c can be enhanced in CoFeB by thermally annealing the junctions - which has been shown to crystallize the layer.^{190,197}

E. Advantages of weak vs strong ferromagnets (length scales)

An important consideration for constructing a π -junction is to consider the ratio of $d_{0-\pi}/\xi_{F1}$. Since the supercurrent decays exponentially with ξ_{F1} , if the 0- π transition occurs at too great of a thickness with respect to ξ_{F1} , the resulting π -junctions will have small critical Josephson currents.

The materials that we can describe as strong ferromagnets in Tables I, II, and IV have $d_{0-\pi}/\xi_{F1}$ ratios which can be ≤ 1 . While this is great for optimizing the critical Josephson current, one of the difficulties of fabricating π -junctions with strong ferromagnetic barriers is that the length scales ξ_{F1} and ξ_{F2} are both short - particularly in the amorphous alloys in Table IV, where ξ_{F1} and ξ_{F2} are < 1 nm. As a result, very precise control over film thickness during deposition is needed to create a thickness series of samples with a small enough increments (step size) to observe the 0- π oscillations. For integrating junctions into an industrial process, the layer thickness margin of error for reproducibility of the π -junction will be small, although sub-nm thick magnetic layers are routinely used in MRAM, so while difficult, this level of control on an industrial scale is not impossible.

Weak ferromagnets offer the advantage that ξ_{F1} and ξ_{F2} can be much longer, up to several nm in the Pd-based weak alloys (Table III), which similarly offer the $d_{0-\pi}/\xi_{F1}$ ratio ≤ 1 . Longer length scales in the Josephson junctions offer the advantage that the parameters of a π -junction, such as J_c , should in principle be more robust against small sample-to-sample variations in the thickness of the barrier. In the weak ferromagnets, CuNi is somewhat of an outlier having a particularly large ratio of $d_{0-\pi}/\xi_{F1}$, causing the critical Josephson current in the π state to be small.

F. Magnetic dead layers and normal metal spacer layers

Ferromagnetic materials are often modelled as slabs with uniform magnetization, however in reality they are rarely so simple. At the interface of a thin magnetic film, it is often observed that the moments of the first few atomic layers may not align, reducing the observed magnetization from the expected one. These are commonly referred to as magnetic dead layers. Furthermore, the presence of such magnetic dead layers can degrade key properties such as the coercive field of the layer. Nb/ferromagnet interfaces are well known for having magnetic dead layers¹⁶⁰ and much effort has been dedicated to studying the related interfacial roughness at Nb/ferromagnet interfaces.^{198,199} Where possible, we have included the thickness of magnetic dead layers in the Tables.

The most reliable method to determine the presence of dead layers is to measure several samples of varying ferromagnet thickness. The magnetometer returns a measurement of the total magnetic moment of the sample which, so long as due care has been taken in the handling of the sample and the data corrections, can be used to report the area normalized magnetic moment.²⁰⁰ If the moment/area is linear with ferromagnet thickness, then the total dead layer thickness (d_i) can be determined according to $\text{moment/area} = M(d_F - d_i)$.

Additional normal metal layers between the Nb and ferromagnet layer are often introduced in the junctions, and we have included such layers as part of the “barrier” in the Tables. These additional layers are commonly referred to in the literature as either buffers, seeds, spacers, or interlayers. Here we will use the term spacer layers to describe any additional normal metal layers. The motivation for adding the spacers is often to provide better lattice matching for the ferromagnet to be deposited.

Considering the example of Co, the fcc spacer layers Cu, Pt and Rh have been studied.

The predicted mechanism is that the fcc spacer layers promote fcc growth of Co, which otherwise may have a mixed fcc/hcp phase. The two desirable benefits that Co grown on the fcc spacer layers gain compared to Co grown directly on Nb is that the magnetic dead layer is reduced or removed completely, and that the improved Co crystal structure can improve supercurrent carrying properties.^{61,159,201}

As a counter example, the inclusion of Cu spacer layers in junctions containing Ni and CuNi alloys may be detrimental. Cu and Ni alloy very readily which can cause the Ni to interdiffuse out of the intended layer and form interfacial alloy layers. Bolginov *et al.*¹⁸⁰ argue that early works on CuNi, Refs. 4 and 178, contain large magnetic dead layers because of interdiffusion of the Ni out of the CuNi layer into an adjacent Cu layer (which was added as a necessary step in the fabrication process). By improving the fabrication process to exclude the extra Cu layer, the resulting junctions without interdiffusion are shown in Table III to have an order of magnitude improvement in $J_c(\pi)$.¹⁸⁰ Kapran *et al.* describe a similar effect comparing single layer Ni and bilayer Cu/Ni junctions, where the former junctions have an order of magnitude higher J_c for the same thickness of Ni.¹⁵⁷ In addition to this Ni specific issue, a known downside of adding normal metal spacer layers is that every interface in the barrier may reduce the critical Josephson current. In particular, normal metals with known large interface resistances should be avoided.²⁰²

A further motivation for adding spacer layers is that they can provide a smoother surface for growing the very thin ferromagnetic layers on compared to Nb. Thin film Nb has a columnar growth of grains which can result in a surface roughness comparable to the thickness of the ferromagnetic barrier layer in a π -junction. Certain metals including Al, Au, and Cu have been shown to act as planarization layers which significantly reduce the surface roughness. We highlight two methods making use of this property as they are employed in works featured in the Tables. The first is to replace the bottom Nb electrode with a superlattice of Nb and a thin normal metal, where the superlattice will have lower surface roughness.²⁰³⁻²⁰⁵ Several works in the Tables use this method, however they are not distinguished in the Tables on the assumption that the use of a thick superlattice is unlikely to affect the reported junction parameters. The second approach is to place a much thinner superlattice on the surface of the single layer Nb electrode in place of the normal metal spacer layer, see Ref. 189 in Table IV.

Barrier	$I_c R_N$ (max) (μV)	J_c (max) (kAcm^{-2})	ΔI_c (P vs AP) (%)	Phase detection	Ref.	Comment
Co/Cu/NiFe	2	20	50		142	
NiFe/Cu/Co	3.5		25		206	
Cu/Ni _{0.70} Fe _{0.17} Nb _{0.13} /Cu/Ni/Cu	4	50	500		143	
Cu/Cu _{0.70} (NiFe) _{0.30} /Cu/NiFe/Cu	1	2.5	380		144	
Ni/Cu/Ni	66	860	210		207	
Cu/NiFe/Cu/Ni/Cu	11	110	93	yes	145	
NiFe/Cu/Ni				yes	147	§
Cu/NiFe/Cu/Ni/Cu	9	90	800		208	
Cu/NiFe/Cu/Ni/Cu	6.5	65	340	yes	146	
Pt/Co/Pt/Co _{0.68} B _{0.32} /Pt	0.5	5	60		209	1.8 K

TABLE V. Summary of literature on Nb based spin-valve Josephson junctions. The full barrier layers, including normal metal spacer layers are listed. For single junction measurements, $I_c R_N$ (max) corresponds to the largest critical Josephson current reported and ΔI_c (P vs AP) is (the difference in I_c between P and AP)/(the lesser of I_c in P or AP) expressed as a percentage, where P is the parallel and AP the antiparallel magnetic alignment. Unless otherwise commented, measurements were performed at 4.2 K. Comments: § The magnetic junctions were passive and therefore the switching parameters were not directly measured.

G. Spin-valve junctions

In Table V we highlight works studying controllable spin-valve junctions.

For spin-valve junctions we extract the parameters that may be useful for potential applications, including the maximum critical Josephson currents, $I_c R_N$ and J_c , achieved in the work, and what was the largest observed difference in critical current between the parallel and antiparallel magnetic alignments. The first quantity is an important consideration where the junction is passive and does not switch (as the critical current must be larger than the active junctions in the circuit) and the second is useful for memory schemes where readout is achieved by measuring directly the state of the spin-valve junction (superconducting or normal) or any other application where large differences between the magnetic alignments is desirable.

It is possible that for the entries in Table V the two magnetic alignments correspond also to a change in phase difference between 0 and π . This can be inferred based on the $0 - \pi$ transition of single layer junctions reported in the other Tables. Direct detection of the phase was achieved in spin-valve junctions by placing the junctions into a phase sensitive SQUID circuit.¹⁴⁵⁻¹⁴⁷

The highest reported critical current in Table V was for a junction where both magnetic layers were pure Ni, which is not surprising from studying the presented Tables for single layer junctions. While using NiFe as the free layer is magnetically beneficial (NiFe has much improved switching properties compared to Ni) the resulting junctions have a much reduced critical current.

V. NON-METALLIC AND EXOTIC π -JUNCTIONS

Ferromagnetic insulators (FIs) have been predicted to show $0-\pi$ transitions.^{54,77,210} Progress in this area has been more difficult due to the limited availability of FI materials, where GdN and Eu chalcogenides have been the most studied for potential integration into superconducting devices. Of the available studies, the only FI material to show a Josephson current in S/FI/S junctions is GdN.⁵⁵ GdN Josephson junctions have shown a range of interesting phenomena, suggesting that the physics inside these junctions is complex.^{55,83,117,192,211-215} Complex behaviors of GdN junctions includes observation of a pure second harmonic current-phase relation.¹¹⁷ We also note an experiment on hybrid junctions containing InAs barriers coated in the FI EuS, where switching between 0 and π coupling is attributed to the magnetic domain structure of the EuS.²¹⁶

Caruso *et al.* studied the thickness and temperature dependence of supercurrent in GdN junctions.¹⁹² The thickness dependence at 0.3 K resulted in an exponential decay, where the fit parameters are shown in Table IV. By studying the temperature dependence of the junctions, the authors characterize an incomplete $0-\pi$ transition with temperature accompanied by spin-triplet physics.¹⁹² Follow up work reports on the possibility to quantitatively describe and eventually control spin-triplet transport through external magnetic fields which is correlated to an “extended” $0 - \pi$ transition in temperature in these GdN FI barriers.²¹⁵

The van der Waals family of materials have only recently been explored in the context of π -junctions. In this case, both the superconductor and magnetic layer must be compatible

with the van der Waals fabrication method, so typically NbSe₂, an *s*-wave superconductor, is used. Reports on junctions and SQUIDs with a barrier of Cr₂Ge₂Te₆ (which is described as either a ferromagnetic semiconductor or ferromagnetic insulator) showed a coexistence of 0 and π phase in the junction region.^{217,218} Another work studied the thickness dependence of S/F/S Josephson junctions with the Cr₂Ge₂Te₆ barrier showing a pronounced minimum in supercurrent at a thickness of 8.4 nm, attributed to the 0 – π transition.¹⁹³ Fitting Eqn 6 to the thickness dependence yields the fit parameters shown on the final line of Table IV. In a planar junction, a long ranged supercurrent was shown across a Fe₃GeTe₂ van der Waals barrier.²¹⁹

The 0 – π transition can occur in Josephson junctions without magnetic barriers if the geometry of the junction allows for Zeeman splitting in a large enough magnetic field. The idea is that in a S/N/S junction, the normal metal in a large enough magnetic field will resemble a weak ferromagnet as the up and down spin bands are displaced by the Zeeman energy.^{220,221} An important factor here is that the applied magnetic field must be parallel to the direction of supercurrent propagation, such that it does not contribute to the Fraunhofer pattern discussed previously. Although an early attempt to observe a so-called Zeeman π -junction with the normal metal Ag by one of the authors was unsuccessful,⁷² later works with non-metallic barriers were successful. Zeeman π -junctions have been realized with barriers of the Dirac semimetal Bi_{1-x}Sn_x,²²² the 2D material graphene,²²³ the topological crystalline insulator SnTe,²²⁴ the two-dimensional electron gas system InSb,^{225,226} and in a quantum dot.²²⁷ In some of the successful implementations, the large g-factors and spin-orbit coupling in these materials contributed along with the Zeeman effect to the observation of 0- π transitions. In the InSb junctions, it was possible to apply a gate voltage which could induce the 0- π transition at a set applied magnetic field.²²⁵

Electron transport across a quantum dot is heavily influenced by the strong Coulomb interaction, including the possibility of observing single electron tunneling.²²⁸ A Josephson junction can be formed across a quantum dot when pairs can coherently tunnel. In a Josephson quantum dot junction, 0 – π transitions are possible by tuning the occupancy levels. Experimental realizations of π -junctions in quantum dots were achieved in an InAs nanowire²²⁹ and in carbon nanotubes.²³⁰⁻²³²

Several examples in this section explore planar junctions, as opposed to the sandwich geometry of all the works presented in the Tables. Planar junctions open additional possi-

bilities for experimental control, such as adding voltage gates and manipulating strain by use of piezoelectric substrate. Another possibility in planar junctions is to control the $0 - \pi$ transition using only the geometry of the junction by introducing curvature.^{233,234}

VI. SPIN-TRIPLET JUNCTIONS

The data in the Tables show clearly that the length scales governing the decay and period of the $0-\pi$ oscillations, ξ_{F1} and ξ_{F2} , are both very short – typically less than 1 nm in the strong F materials and up to several nm in the weak F materials. In the late 1990’s, however, there were some experimental hints of a long-range proximity effect in S/F systems based on measurements of the electrical resistance of long F wires connected to an S electrode.^{235–237} Those results foreshadowed the 2001 theoretical breakthrough by Bergeret *et al.* mentioned in the Introduction. Further experimental support for the theory appeared in 2006,^{238,239} but the experimental breakthroughs that finally convinced the skeptics in the community did not appear until 2010.^{50,165,240,241} Those works all showed that the supercurrent in an S/F/S junction decayed over a distance much longer than ξ_F if the F layer contained the appropriate kind of noncollinear magnetization needed to convert spin-singlet Cooper pairs from the S electrodes into spin-triplet pairs in the central region of the junction. In the case of the “half-metal” CrO_2 , a supercurrent can propagate hundreds of nanometers through the F material.^{50,242} Since that time, there have been several reviews of spin-triplet proximity effects in S/F systems;^{21–24,243} we do not review that large body of work here.

A. Controllable π -junctions

Very few experimental studies of spin-triplet supercurrents address the issue of the ground-state phase difference across the junction. The theoretical papers, however, make specific predictions about this issue.^{20,244–248} Here we discuss only the sample geometry suggested by Houzet and Buzdin in 2007,²⁴⁴ which was realized in many experiments. In that theoretical work, the sequence of layers in the junction is S/F'/F/F''/S, where the directions of the magnetizations of the three F layers can be controlled independently. (In experimental devices, normal spacer layers are placed between adjacent F layers to prevent exchange coupling between them.) In particular, the magnetizations \mathbf{M} of any two adjacent layers

must be non-collinear; let us choose adjacent layers to have orthogonal magnetizations to maximize generation of spin-triplet supercurrents. If we define the direction of \mathbf{M}' as the z-direction and the direction of \mathbf{M} as the x-direction, and if we keep all three magnetizations coplanar, then the direction of \mathbf{M}'' may be either plus or minus z. According to theory, the former case produces a π -junction whereas the latter produces a 0-junction.^{20,244–246} The only experimental work that tests this prediction, to our knowledge, is the one by Glick *et al.* in 2018.²⁴⁹ To achieve the required orthogonal magnetizations, those authors used a Pd/Co multilayer with perpendicular anisotropy as the central F layer. (Actually, two such multilayers were placed back-to-back separated by a Ru spacer layer to achieve a synthetic antiferromagnet. That does not change the 0 – π physics, according to theory.^{245,246}) Those authors used Ni as the fixed F'' layer and NiFe as the free F' layer. Seven out of eight junctions showed robust π phase switching when the direction of the NiFe magnetization was reversed by a small applied field.

From a practical perspective, spin-triplet junctions appear less attractive than the simpler spin-valve junctions discussed in Section III C. They do have one advantage, however: the constraints on the thicknesses of the F layers needed for switching between the 0 and π states of the junctions are less stringent in the case of spin-triplet junctions than they are for spin-valve junctions.²⁵⁰

B. ϕ and ϕ_0 -junctions

The spin-singlet physics discussed in the majority of this article would appear to allow only junctions with ground-state phase differences of 0 or π . That is not true, however. A spatially-extended junction containing only a single F layer with varying thickness, such that some parts of the junction prefer the 0-state while others prefer the π -state, can have degenerate ground states at phases $\pm\phi$.^{251–255} Such junctions are called “ ϕ -junctions,” where the phase ϕ can take any value between 0 and π . Such junctions still obey the conventional time-reversal symmetry relation, $I_s(-\varphi) = -I_s(\varphi)$, where φ is the phase difference between the superconducting condensates in the two S electrodes.

Spin-triplet junctions containing three F-layers have an additional possibility, if the three magnetizations are non-coplanar. In that case, time-reversal symmetry is broken, and cannot be restored by a simple rotation of the entire spin system.²⁵⁶ Such junctions may have a

ground-state phase difference of ϕ_0 , which can take any value between 0 and 2π , and is nondegenerate on that interval. Such junctions are now called ϕ_0 -junctions, to distinguish them from the ϕ -junctions discussed in the previous paragraph. The existence of ϕ_0 -junctions was predicted in a number of theoretical works starting in 2007,²⁵⁶⁻²⁶⁶ and two reviews have appeared recently.^{267,268} Because of the broken symmetries, ϕ_0 -junctions do not obey $I_s(-\varphi) = -I_s(\varphi)$, hence this phenomenon is also referred to as the “anomalous Josephson effect”, or AJE. Since 2016, the AJE has been experimentally observed in a wide variety of exotic systems with strong spin-orbit interaction^{218,269-275} and in planar out-of-equilibrium devices,²⁷⁶ but so far it has not been observed in metallic sandwich junctions.

VII. OPEN CHALLENGES AND OUTLOOK

We hope that the presented Tables act as both a record of current literature and inspiration for the future direction of the field. While magnetic π -junctions are somewhat of a mature field, we feel from the presented Tables that a Goldilocks junction material that passes a large supercurrent in the π -state while having well controlled magnetic properties is still to be discovered. Such a material is particularly needed to realize practical spin-valve junctions. In this section, we outline some open challenges and provide an outlook on the field.

A. Spread in junction parameters and influence of fabrication method

From examination of the Tables in this work, the reader may find themselves overwhelmed with seemingly contradictory information on the same material - a thickness of ferromagnet that provides a π -state from one work may not directly translate to the π -state in another work. For Ni and NiFe, the two most studied barriers, the authors have directed the reader towards what they consider to be the most reliable value for the thickness $d_{0-\pi}$.

In some cases, the explanation for spread in the Tables may be as simple as differences in the way the ultra-thin layer thicknesses were calibrated, or that the range of thicknesses studied unintentionally missed a $0 - \pi$ transition. In other cases, the explanation may be more complex. The decay length inside the ferromagnet, ξ_{F1} , is shown in the Tables to vary considerably between works. This parameter is sensitive to the exact layer morphology,

which itself is influenced by the presence or absence of normal metal spacer layers. We also must consider what role, if any, does the junction fabrication process have on the measured parameters in the Tables. Bolginov *et al.* provide a detailed account of improvements made to their fabrication process, which resulted in a significant difference to the parameters, particularly the thickness of $d_{0-\pi}$, in junctions measured with CuNi barriers.¹⁸⁰

Two common fabrication methods are based around either the ion beam etching or focused ion beam techniques, which are described in detail elsewhere.^{204,277} Here, we highlight a significant difference in the two methods which may affect junction parameters. The ion beam etching process typically requires that the top Nb electrode be deposited separately to the bottom Nb electrode and barrier layers, post-fabrication and etching. To protect the barrier layers from oxidation during fabrication, a normal metal capping layer must be added above the barrier layers. In focused ion beam fabrication, both bottom and top electrodes as well as the barrier layers can be deposited in the same vacuum cycle, meaning no additional capping layers are required by the processing. We speculate that this difference may account for the generally higher critical Josephson currents observed in focused ion beam junctions, although there has been no systematic study comparing the two techniques to date.

Based on the discussion in this section, the authors highly recommend that while the Tables in this work can be used to help choose materials to implement as π -junctions in an application, that researchers don't assume that parameters provided in the Tables will exactly reproduce in their own process. It is therefore necessary to conduct a full systematic study of a material using the deposition and fabrication methods needed for the ultimate application to determine the exact parameters for junctions produced by that process.

B. Magnetic initialization

In the as-grown state, the direction of the F layer's magnetization in a junction may be uncontrolled and could have broken up into magnetic domains. In a single F layer junction, the physics driving the $0 - \pi$ oscillations should not depend on the direction of magnetization. However, for in-plane magnetization, the Fraunhofer pattern of an individual junction can be strongly influenced by the direction and domain state of the F layer, as discussed in Section IID. Since determining the critical Josephson current in the junction relies on interpretation of the Fraunhofer response, it may be preferable to initialize the magnetization to

a known direction and to minimize domains. Another case where setting the magnetization direction of the ferromagnet in the junction is crucial are spin-valve junctions, where it is essential to know and control the relative orientations of the magnetic layers. For junctions with perpendicular magnetic anisotropy, the magnetization is perpendicular to the applied field so the Fraunhofer pattern should be less influenced and therefore magnetic initialization may not be necessary.

To aid control of the in-plane magnetization direction in a junction, it is usual to create a shape anisotropy by defining the junction area as an ellipse, where it is favourable for the magnetization to point in the long axis. Even with a shape anisotropy, for a single domain F layer, there are now two directions that the magnetization could point. When the magnetic domains are small the situation is worse, as the magnetic layer may break up into domains pointing in many different directions, and stray magnetic fields may emerge from the domain walls.

The standard procedure, to set the direction of magnetization and minimize the number of domains, is to initialize the magnetic layer in a large magnetic field. The magnetic field must be applied while the circuit is far below the Curie temperature – which might be below room temperature in the case of very thin magnetic layers – but above the superconducting critical temperature of Nb to avoid flux trapping. For Ni, where the small domain size is particularly problematic, it is typical to apply a global initialization field of ≥ 350 mT to saturate the Ni magnetization.¹⁵⁵ A superconducting digital logic circuit is unlikely to be implemented in a cryogenic environment which includes the ability to apply a large global field, hence it would be favourable to have a magnetic layer which forms a single magnetic domain and does not require an initialization field procedure.

In some materials, such as NiFe, magnetic anisotropy can be set by a growth field during deposition, which may be enough to set the direction of magnetization without the need for additional initialization fields. Another mechanism which can set the magnetization is the exchange bias effect between a ferromagnetic and antiferromagnetic material.²⁷⁸ However, it has been found that supercurrent is severely suppressed in Josephson junctions containing metallic antiferromagnetic barriers.^{279–281}

C. Materials compatibility with Nb or CMOS fab (MRAM example)

MRAM is an example where integrating the magnetic junctions into the traditional CMOS wafer fabrication has been extremely difficult. Generally, the magnetic layers of the MRAM are incompatible with the CMOS process. One of the reasons for this is that elevated temperatures used for the CMOS process would cause the thin magnetic layers to interdiffuse. The solution is that the standard CMOS wafer is manufactured in one front-end-of-the-line facility, then shipped to a separate facility for backend-of-the-line processing, where the MRAM is built. This approach has several technological disadvantages, including severely limiting circuit design possibilities.

For superconducting electronics, although a multi-facility approach is possible without compromising the overall transport properties of individual junctions,^{92,109,110,282,283} in our opinion it would be best to avoid the multi-facility approach so that circuit design is not limited. In 2019, MIT Lincoln Laboratory announced a new fabrication process for superconductor electronics called PSE2, which integrates Ni π -junctions - an important step towards using π -junctions in logic circuits.¹⁵⁶ But we are not aware of any published circuit demonstrations using that process. As we have previously motivated, pure Ni may not be the ideal choice of material due to the high initialization field required and small magnetic domains.

The Tables presented here might motivate the reader to revisit pure Fe or to pursue other Fe containing alloys (NiFe, PdFe, etc.) as potential π -junction materials. However, we would urge caution on exploring further materials that include Fe when considering incorporation into an integrated fabrication process. Fe may be incompatible with scaled fabrication processes due to the potential detrimental effect Fe contamination would have on the rest of the process.

Our conclusion from a materials compatibility perspective is that Ni based alloys are well motivated for further work, particularly those that are in the limit Kapran *et al.* describe as “strong-but-clean”, meaning strong ferromagnetism with ballistic transport properties.¹⁵⁷ We also mention that it may be possible to explore alloys and compounds for magnetic barriers where the component materials are otherwise non-magnetic, such as PdMn,²⁷ some Heuslers,^{241,284} and $L1_0$ -ordered MnAl²⁸⁵ or MnGa.²⁸⁶ Such an approach may negate any concerns about ferromagnetic particle contamination in a Nb process.

D. Materials and read/write operations for spin-valves

We identify some outstanding challenges specific to spin-valve junctions. Firstly, to achieve a spin-valve junction with high critical current, it seems necessary to replace the NiFe free layer. Secondly, we must remove the requirement for global magnetic field for read/write operations and move towards on-chip operations.

The materials for spin-valve junctions have several requirements and important considerations: the fixed layer must be robust enough against the switching of the free layer, both layers should be single domain so that the supercurrent and phase difference across the junction is uniform, both layers must be sufficiently thin to allow a significant supercurrent to propagate through the junction, magnetic dead layers (which can dominate in very thin layers) must be minimized, and the $0 - \pi$ oscillations of each component layer must be well characterized. It is not obvious from the Tables presented in this work that there is an immediate replacement for either NiFe as the free layer or Ni as the fixed layer.

On the prospect of on-chip writing, we note that there are adventurous proposals for switching magnetic layers in the superconducting state of S-F systems,²⁸⁷⁻²⁹⁰ although there is not yet experimental realization. We therefore suggest that established mechanisms used in the field of spintronics and technologies for MRAM can also be applied in the normal state of a superconducting spin-valve. Spin transfer torque switching, where a current pulse is passed through the junction and induced magnetization dynamics causes the free layer to switch, was demonstrated by Baek *et al.* by applying a current density to their junction which greatly exceeded J_c .²⁰⁷ Spin orbit torque switching, where a current pulse is passed through a layer with large spin Hall angle adjacent to the free layer causing it to switch, has shown promising results in room-temperature magnetic tunnel junctions, and promises faster switching speeds than spin transfer torque.²⁹¹ Raytheon BBN Technologies have proposed a low temperature superconductor-ferromagnet hybrid memory (not based on the Josephson effect) where magnetic switching is achieved by spin Hall effect.²⁹²

E. Altermagnets

Solids with an intrinsic magnetic phase are traditionally classed as having either ferromagnetic or antiferromagnetic ordering. Recently, there has been great interest in the

fundamental study and potential applications of an emerging third class of magnetic solid, where the magnetic phase is known as altermagnetism.²⁹³ Altermagnets have properties that blur the lines between the traditional ferromagnetic and antiferromagnetic orderings. On the one hand, these materials have electronic properties consistent with ferromagnetism, they show an anomalous Hall effect and have spin-polarized conduction bands. On the other hand, altermagnetic materials have antiparallel magnetic crystal order and zero net magnetization, consistent with antiferromagnetism. Altermagnets are expected to be abundant in nature.²⁹³

The presence of a spin-polarized conduction band suggests that much of the rich physics present in ferromagnet-superconductor hybrid systems are also present when the ferromagnet is replaced by an altermagnet, along with additional unique physics in the new altermagnet system. Notably in the altermagnet, the finite pair momentum appears in the absence of a net magnetization.²⁹⁴ Zero net magnetic moment junctions offers the significant advantages over ferromagnet systems that the junctions produce either zero or negligibly small stray magnetic fields, and they don't require any magnetic initialization.

Of particular interest to the topic of this review are predictions of $0-\pi$ oscillations in Josephson junctions containing altermagnetic barriers.²⁹⁴⁻²⁹⁷ To date, there are no experimental studies of altermagnet-superconductor hybrid systems. The most studied candidate altermagnet is RuO_2 , a metal with a bulk room-temperature resistivity of $\rho \approx 35 \mu\Omega\text{-cm}$.²⁹⁸

F. Neuromorphic and novel analogue computing

Magnetic Josephson junctions have been proposed as artificial synapses for neuromorphic computing schemes.²⁹⁹⁻³⁰¹ Neuromorphic computing is seen as a potential solution to the problem of poor energy efficiency when running neural networks on traditional computing architectures. The Tutorial of Schneider *et al.* covers the topic of neuromorphic systems based on magnetic Josephson junctions in detail.³⁰² Here we focus on the materials and requirements for this application.

The requirements in this potential application is for the junction to provide a continuously tunable (analogue) response, provide a degree of plasticity/memory, and be scalable and energy efficient enough for the architecture required to interconnect many such devices needed for neuromorphic application.

So far, synapse behavior in magnetic Josephson junctions has been achieved in magnetic nanoclusters. The magnetic clusters do not spontaneously order, but can be aligned by subsequent current pulses. The magnetic order can be tuned continuously from the disordered to ordered magnetic states, and the degree of order affects the critical current of the junction.³⁰²⁻³⁰⁵ Similar to the π -junctions presented in the Tables, there will be a wide variation of performance in metrics such as the $I_c R_N$ of barriers with different magnetic nanoclusters. We are aware of two magnetic nanocluster barriers which have been studied for this application, Mn clusters embedded in Si³⁰³ and Fe clusters embedded in Ge.³⁰⁴ Current limitations are that the $I_c R_N$ products in these barriers are quite a low and the Mn clusters in Si required an annealing step. A potential alternative to nanoclusters are ultra-thin magnetic layers, sometimes called dusting layers, which can also be close to the superparamagnetic transition.

VIII. CONCLUSIONS

Readers new to this field may be overwhelmed by the sheer number of materials listed in the Tables in Section IV, as well as the wide variability in parameters extracted by different research groups. To avoid that parting impression, we finish the review by expressing a few of our own opinions.

First, if we had to choose a material from the Tables to make highly-reproducible π -junctions that can tolerate small variations in thickness, we would choose a PdNi alloy with a Ni concentration in the range of 10 - 15%. Pham *et al.* report values of J_c and $I_c R_N$ in the π -state as large as 70 kA/cm² and 18 μ V, respectively, in Pd₈₉Ni₁₁ junctions with NbN superconducting electrodes.¹⁸³ Because of its mild perpendicular anisotropy, junctions containing PdNi may not need magnetic initialization. The only drawback of this material is the cost of Pd; but we remind readers that only very small amounts of the material are needed.

Second, if one wants the highest possible critical current density in a π -junction, then Ni is the obvious choice. But Ni junctions require magnetic initialization in a rather large magnetic field to establish a reproducible magnetized initial state. Without that initialization, the Fraunhofer pattern will vary randomly from sample to sample, yielding non-reproducible values of J_c .

Third, if one wants a magnetically-soft free layer for a spin-valve junction, then NiFe is the best choice so far. Our own attempts to dilute NiFe to lower its magnetization (and hence the magnetic switching energy) have been largely unsuccessful; in the case of doping with Mo or Cr, the resulting material has a short mean free path, leading to a steep decay of J_c with thickness.

And finally, we lament the heavy use of CuNi alloy by groups new to the field. We acknowledge the many “firsts” achieved by the Ryazanov group and their collaborators using junctions containing CuNi, but the high rate of spin-flip scattering in the material causes J_c to decay very steeply with thickness, leading to very small values of J_c and $I_c R_N$ in the π -state. The main advantages of CuNi are: i) ξ_F is long due to the small magnetization, so thickness fluctuations are tolerated; ii) the perpendicular anisotropy avoids distortions of the Fraunhofer pattern; and iii) the material is less expensive than PdNi. We would recommend using that material only when junction size is not an issue, so that the small value of J_c is tolerated. But we much prefer PdNi alloy.

In summary, we believe that π -junctions have an important role to play in the development of superconducting digital electronics. We hope that this review will help workers navigate the vast literature as they explore new materials for π -junctions.

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AUTHOR DECLARATIONS

Conflict of Interest

The authors have no conflicts to disclose.

Author Contributions

N.O. Birge: writing - original draft (equal) **N. Satchell:** writing - original draft (equal)

DATA AVAILABILITY

Data sharing is not applicable to this article as no new data were created or analyzed in this study.

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